



3 GHz N N/O S.P.4 T. SWITCH

OPTIONS : / TTL DRIVE /SUPP.DIODES

**R F CHARACTERISTICS**

NUMBER OF WAYS : 4  
FREQUENCY RANGE : 0 - 3 GHz  
IMPEDANCE : 50 Ohms

FREQUENCY (GHz)	0 - 3
V.S.W.R	<= 1.20
INSERT. LOSS <=	0.20 dB
ISOLATION >=	80 dB
AVER. POWER (*)	300 W

**ELECTRICAL CHARACTERISTICS**

ACTUATOR : NORMALLY OPEN  
NOMINAL CURRENT AT 25° C (±10%) : 250 mA  
ACTUATOR VOLTAGE (Vcc) : 12V (10.2 to 13V) / NEGATIVE COMMON  
TERMINALS : solder pins (250°C max./30 sec.)  
TTL INPUTS (E) - High level : 2.2 to 5.5V / 800µA at 5V  
- Low level : 0 to 0.8V / 20µA at 0.8V

**MECHANICAL CHARACTERISTICS**

CONNECTORS : N female per MIL C 39012  
LIFE : 2.000.000 cycles per position  
SWITCHING TIME (nominal voltage;25° C) : < 15 ms  
CONSTRUCTION : splashproof  
WEIGHT : < 460 g

**ENVIRONMENTAL CHARACTERISTICS**

OPERATING TEMPERATURE RANGE (°C) : -40 , +85  
STORAGE TEMPERATURE RANGE (°C) : -55 , +85

(\* : average power at 25° C per RF path)

4112-9212 This information is given as an indication. In the continual goal to improve our products, we reserve the right to make any modifications judged necessary

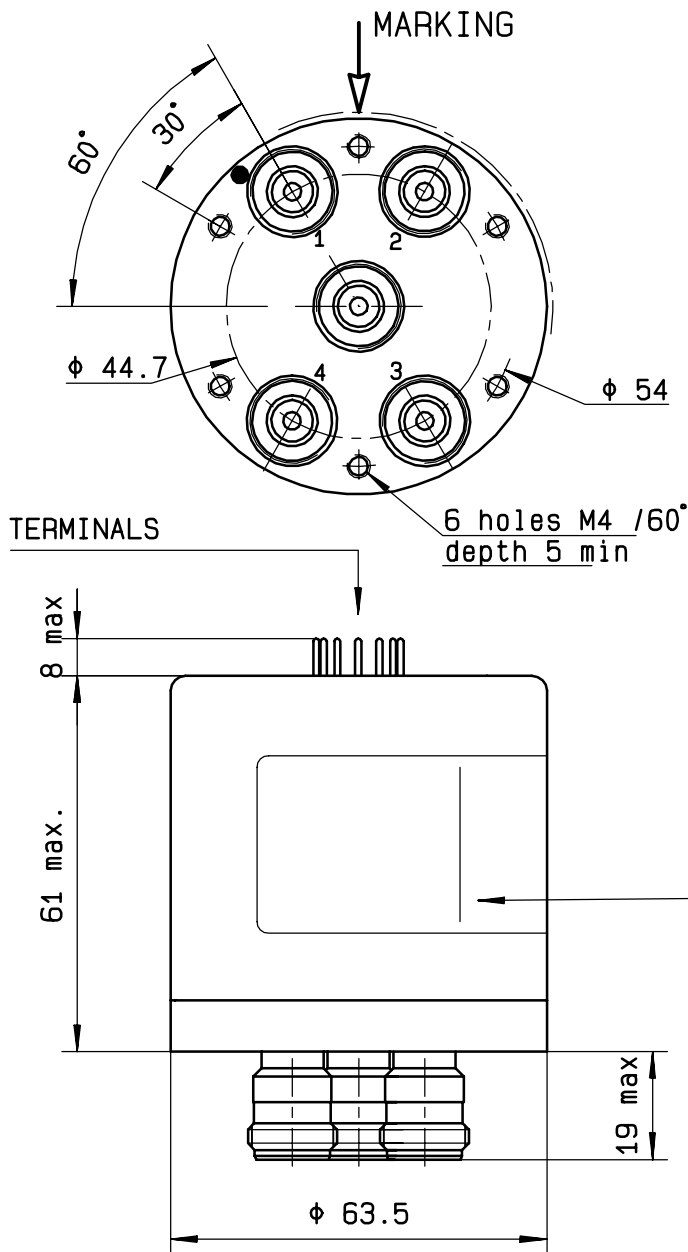
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**DRAWING**

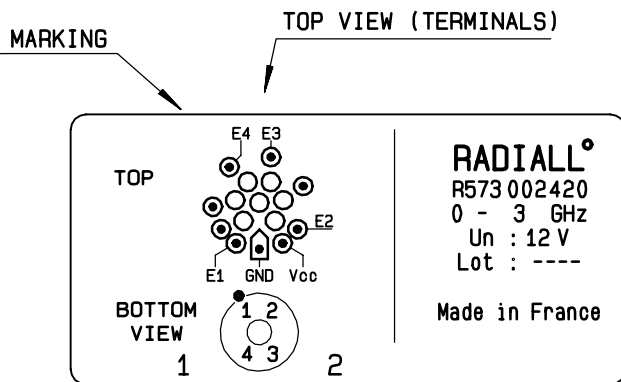
General tolerance: ± 0,5 mm

**R573 002 420**

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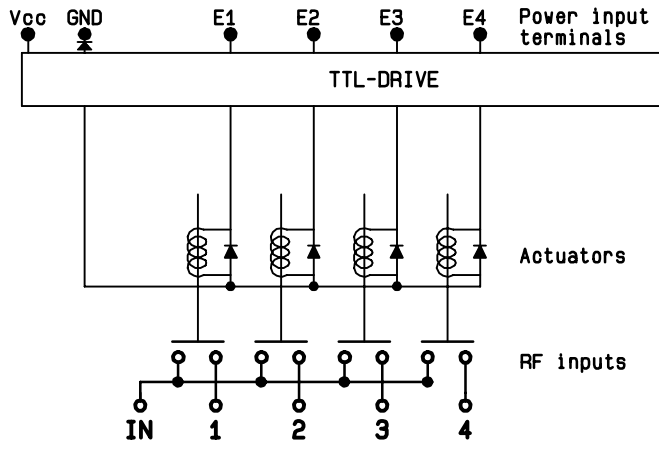


TTL input	RF continuity
E1 = 1	IN ↔ 1
E2 = 1	IN ↔ 2
E3 = 1	IN ↔ 3
E4 = 1	IN ↔ 4



**RADIALL<sup>o</sup>**  
R573 002420  
0 - 3 GHz  
Un : 12 V  
Lot : ----  
Made in France

**SCHEMATIC DIAGRAM**



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